

Cool MOS™ Power Transistor



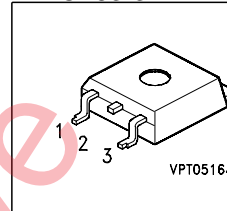
Feature

- New revolutionary high voltage technology
- Worldwide best $R_{DS(on)}$ in TO 220
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- Ultra low effective capacitances
- Improved noise immunity
- 150 °C operating temperature

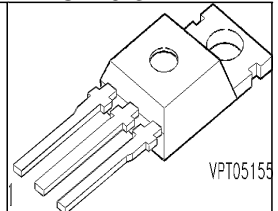
Product Summary

$V_{DS} @ T_{jmax}$	650	V
$R_{DS(on)}$	3	mΩ
I_D	1.8	A

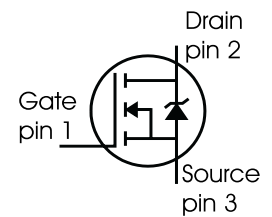
P-TO263-3-2



P-TO220-3-1



Type	Package	Ordering Code	Marking
SPP02N60C3	P-TO220-3-1	Q67040-S4392	02N60C3
SPB02N60C3	P-TO263-3-2	Q67040-S4393	02N60C3



Maximum Ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current	I_D	1.8	A
$T_C = 25\text{ °C}$		1.8	
$T_C = 100\text{ °C}$		1.1	
Pulsed drain current, t_p limited by T_{jmax}	$I_{D\text{ puls}}$	5.4	
Avalanche energy, single pulse	E_{AS}	50	mJ
$I_D=0.9\text{A}, V_{DD}=50\text{V}$			
Avalanche energy, repetitive t_{AR} limited by T_{jmax} ¹⁾	E_{AR}	0.07	
$I_D=1.8\text{A}, V_{DD}=50\text{V}$			
Avalanche current, repetitive t_{AR} limited by T_{jmax}	I_{AR}	1.8	A
Reverse diode dv/dt	dv/dt	6	V/ns
$I_S=1.8\text{A}, V_{DS} < V_{DD}, di/dt=100\text{A}/\mu\text{s}, T_{jmax}=150\text{°C}$			
Gate source voltage static	V_{GS}	±20	V
Gate source voltage dynamic	V_{GS}	±30	
Power dissipation, $T_C = 25\text{°C}$	P_{tot}	25	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	°C

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	5	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
SMD version, device on PCB: @ min. footprint @ 6 cm ² cooling area ²⁾	R_{thJA}	-	-	62	
		-	35	-	
Linear derating factor		-	-	0.2	W/K
Soldering temperature, 1.6 mm (0.063 in.) from case for 10s	T_{sold}	-	-	260	°C

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Static Characteristics

Drain-source breakdown voltage $V_{GS}=0V, I_D=0.25mA$	$V_{(BR)DSS}$	600	-	-	V
Drain-source avalanche breakdown voltage $V_{GS}=0V, I_D=0.25A$	$V_{(BR)DS}$	-	700	-	
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = 80\ \mu A$	$V_{GS(th)}$	2.1	3	3.9	
Zero gate voltage drain current $V_{DS} = 600\ V, V_{GS} = 0\ V, T_j = 25\text{ °C}$ $V_{DS} = 600\ V, V_{GS} = 0\ V, T_j = 150\text{ °C}$	I_{DSS}	-	0.5	1	μA
		-	-	50	
Gate-source leakage current $V_{GS}=20V, V_{DS}=0V$	I_{GSS}	-	-	100	nA
Drain-source on-state resistance $V_{GS}=10V, I_D=1.1A, T_j=25\text{ °C}$ $V_{GS}=10V, I_D=1.1A, T_j=150\text{ °C}$	$R_{DS(on)}$	-	2.7	3	m Ω
		-	6	6.7	
Gate input resistance $f = 1\text{ MHz}$, open drain	R_G	-	9	-	Ω

¹ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV} = E_{AR} \cdot f$.

² Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics , at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Characteristics						
Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 1.1\text{A}$	-	1.75	-	S
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$,	-	200	-	pF
Output capacitance	C_{oss}	$f = 1\text{MHz}$	-	90	-	
Reverse transfer capacitance	C_{rss}		-	4	-	
Effective output capacitance, 1) energy related	$C_{o(er)}$	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V}$ to 480V	-	8.1	-	pF
Effective output capacitance, 2) time related	$C_{o(tr)}$		-	15.7	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 350\text{V}$, $V_{GS} = 0/10\text{V}$,	-	8	-	ns
Rise time	t_r	$I_D = 1.8\text{A}$, $R_G = 50\Omega$	-	5	-	
Turn-off delay time	$t_{d(off)}$		-	45	70	
Fall time	t_f		-	20	30	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD} = 420\text{V}$, $I_D = 1.8\text{A}$	-	1.6	-	nC
Gate to drain charge	Q_{gd}		-	3.8	-	
Gate charge total	Q_g	$V_{DD} = 420\text{V}$, $I_D = 1.8\text{A}$, $V_{GS} = 0$ to 10V	-	9.5	12.5	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 420\text{V}$, $I_D = 1.8\text{A}$	-	5.5	-	V

¹ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

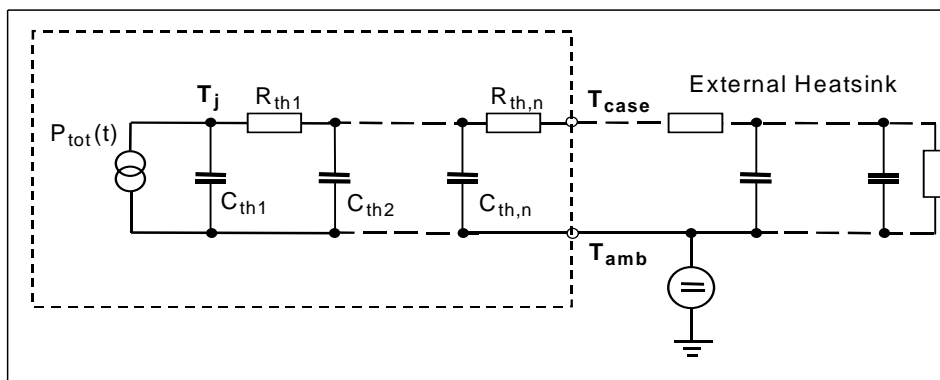
² $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Characteristics						
Inverse diode continuous forward current	I_S	$T_C=25^\circ\text{C}$	-	-	1.8	A
Inverse diode direct current, pulsed	I_{SM}		-	-	5.4	
Inverse diode forward voltage	V_{SD}	$V_{GS}=0\text{V}, I_F=I_S$	-	1	1.2	V
Reverse recovery time	t_{rr}	$V_R=420\text{V}, I_F=I_S,$	-	200	350	ns
Reverse recovery charge	Q_{rr}	$di_F/dt=100\text{A}/\mu\text{s}$	-	1.3	-	μC
Peak reverse recovery current	I_{rrm}		-	9	-	A
Peak rate of fall of reverse recovery current	di_{rr}/dt		-	-	200	$\text{A}/\mu\text{s}$

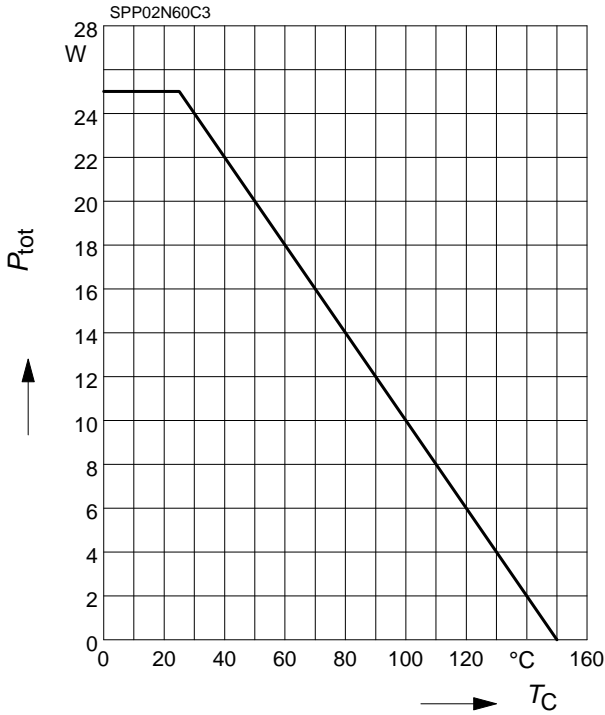
Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
Thermal resistance			Thermal capacitance		
R_{th1}	0.101	K/W	C_{th1}	0.00003158	Ws/K
R_{th2}	0.207		C_{th2}	0.0001104	
R_{th3}	0.311		C_{th3}	0.0002001	
R_{th4}	0.583		C_{th4}	0.0004898	
R_{th5}	0.501		C_{th5}	0.00274	
R_{th6}	0.135		C_{th6}	0.035	



1 Power dissipation

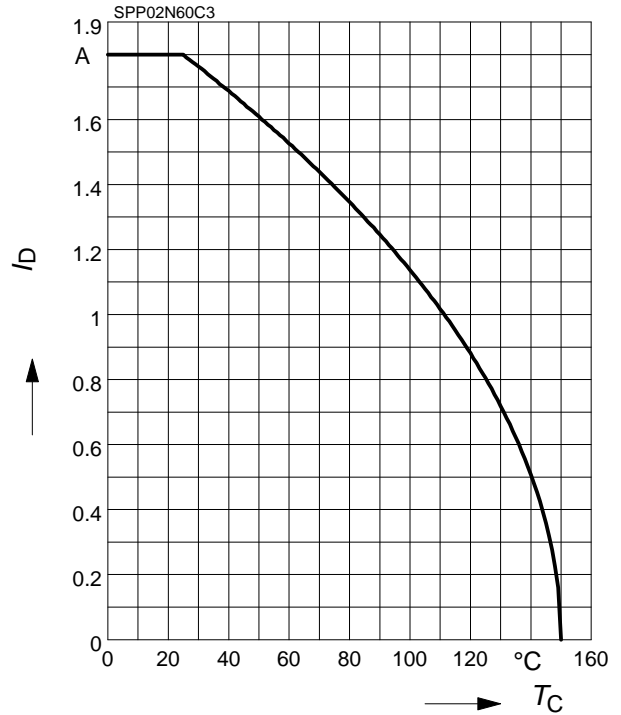
$$P_{\text{tot}} = f(T_C)$$



2 Drain current

$$I_D = f(T_C)$$

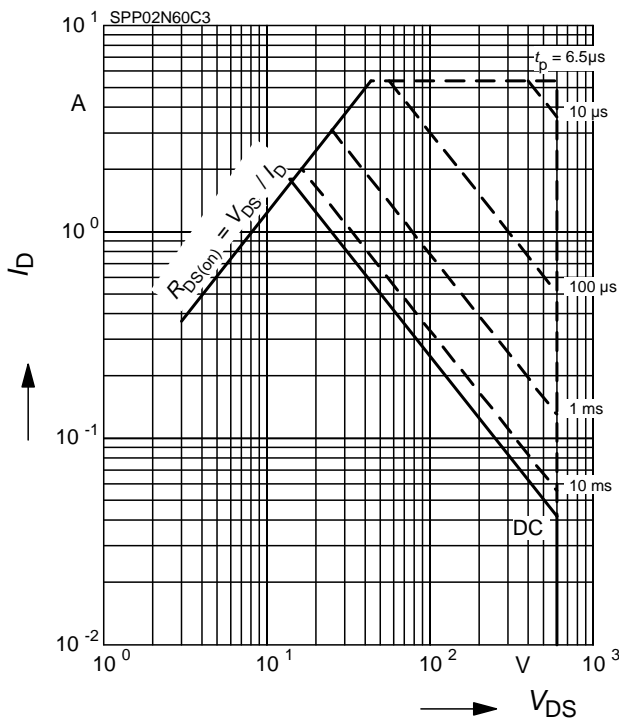
parameter: $V_{GS} \geq 10 \text{ V}$



3 Safe operating area

$$I_D = f(V_{DS})$$

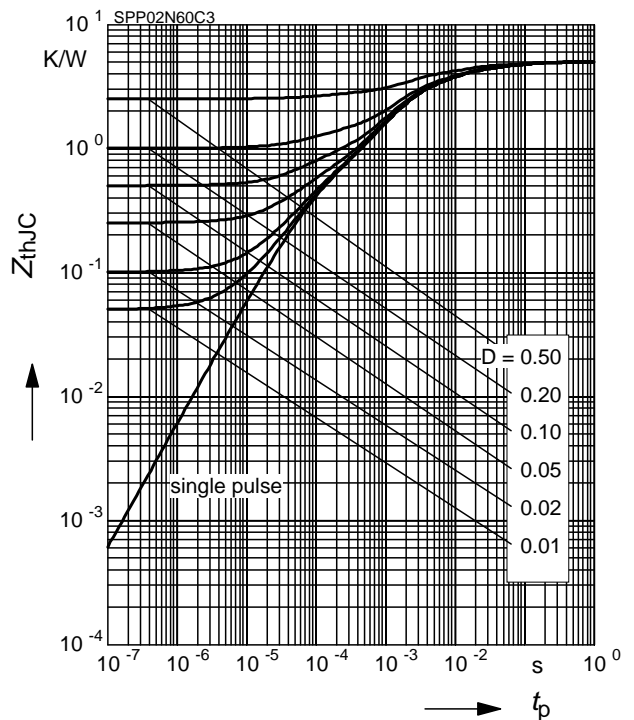
parameter: $D = 0$, $T_C = 25^\circ\text{C}$



4 Transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

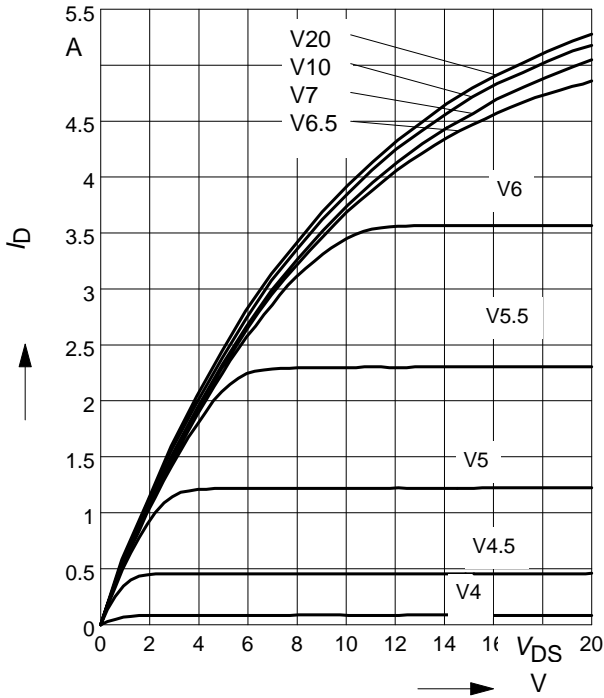
parameter: $D = t_p/T$



5 Typ. output characteristic

$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

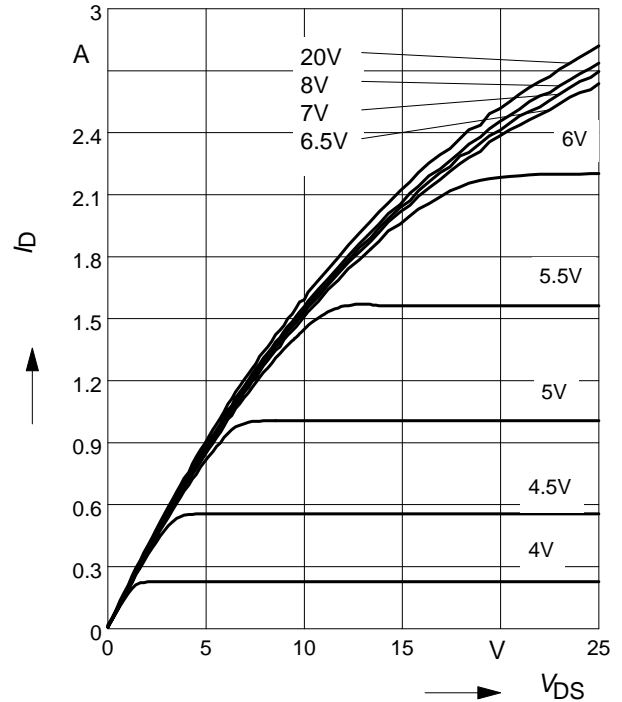
parameter: $t_p = 10 \mu\text{s}, V_{GS}$



6 Typ. output characteristic

$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$

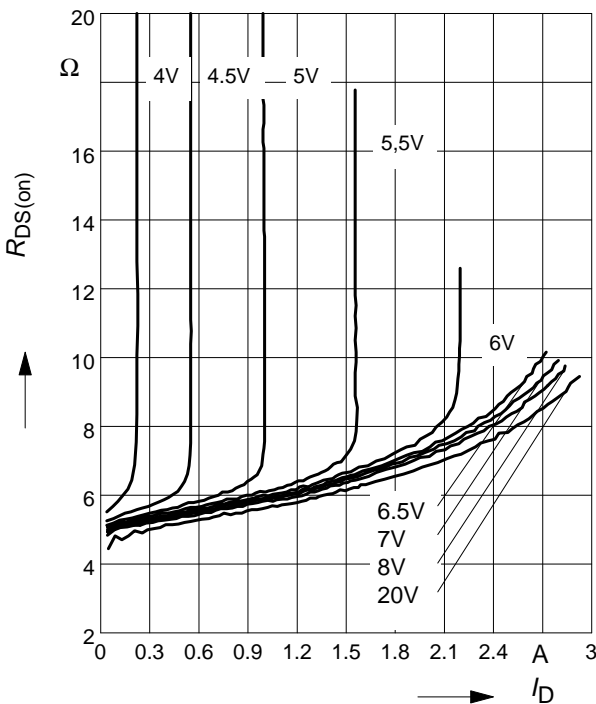
parameter: $t_p = 10 \mu\text{s}, V_{GS}$



7 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D)$

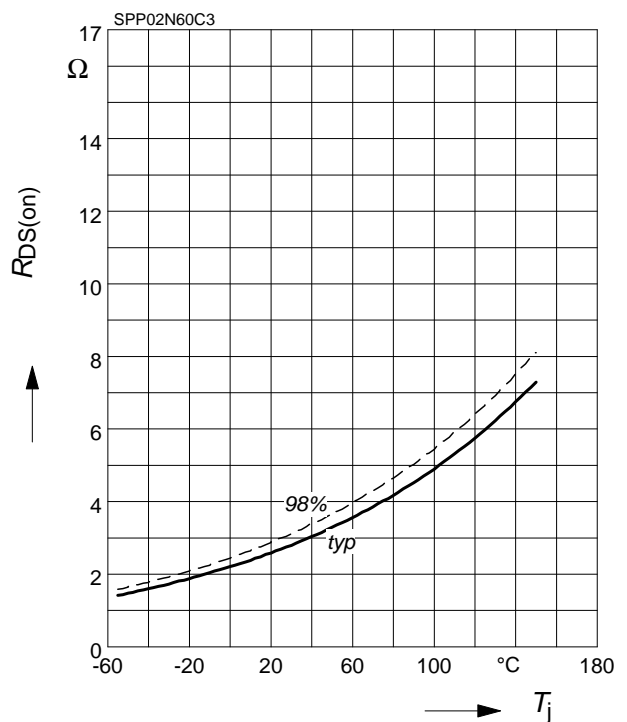
parameter: $T_j = 150^\circ\text{C}, V_{GS}$



8 Drain-source on-state resistance

$R_{DS(on)} = f(T_j)$

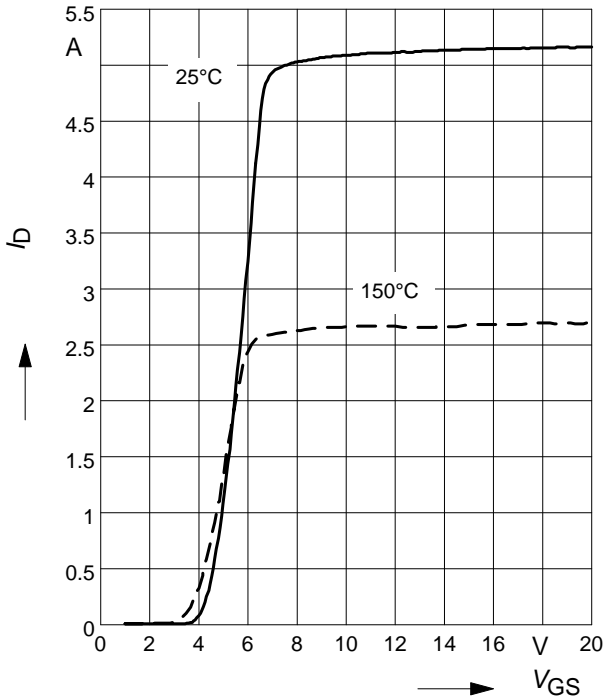
parameter: $I_D = 1.1 \text{ A}, V_{GS} = 10 \text{ V}$



9 Typ. transfer characteristics

$I_D = f(V_{GS})$; $V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

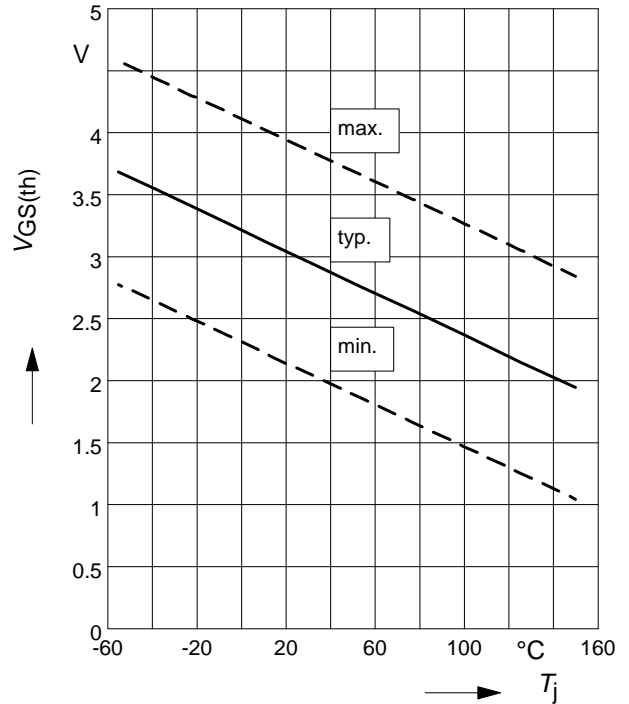
parameter: $t_p = 10 \mu s$



10 Gate threshold voltage

$V_{GS(th)} = f(T_j)$

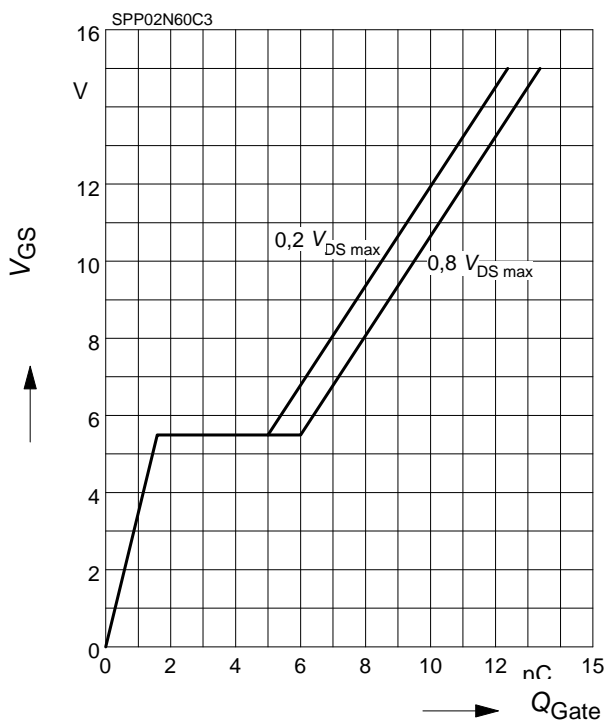
parameter: $V_{GS} = V_{DS}$, $I_D = 80 \mu A$



11 Typ. gate charge

$V_{GS} = f(Q_{Gate})$

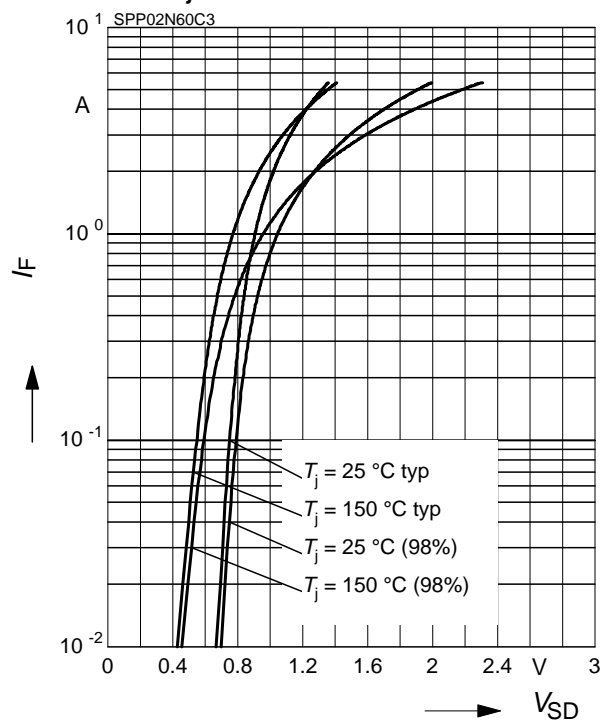
parameter: $I_D = 1.8 A$ pulsed



12 Forward characteristics of body diode

$I_F = f(V_{SD})$

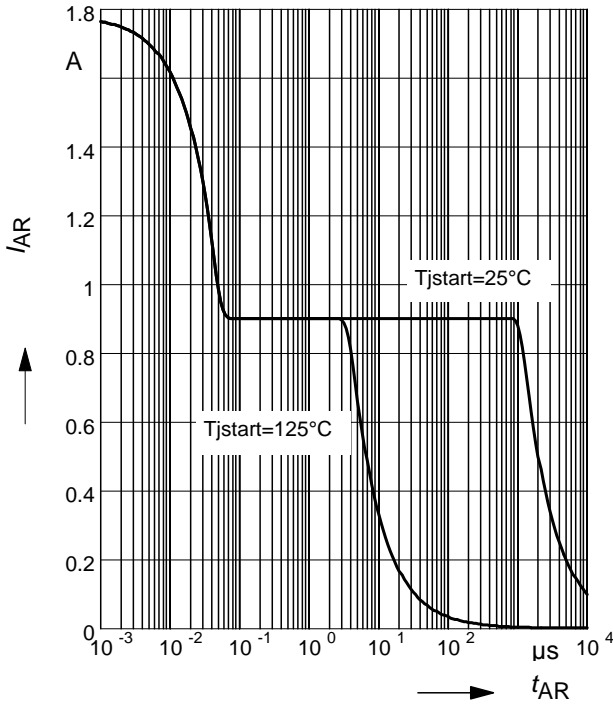
parameter: T_j , $t_p = 10 \mu s$



13 Avalanche SOA

$$I_{AR} = f(t_{AR})$$

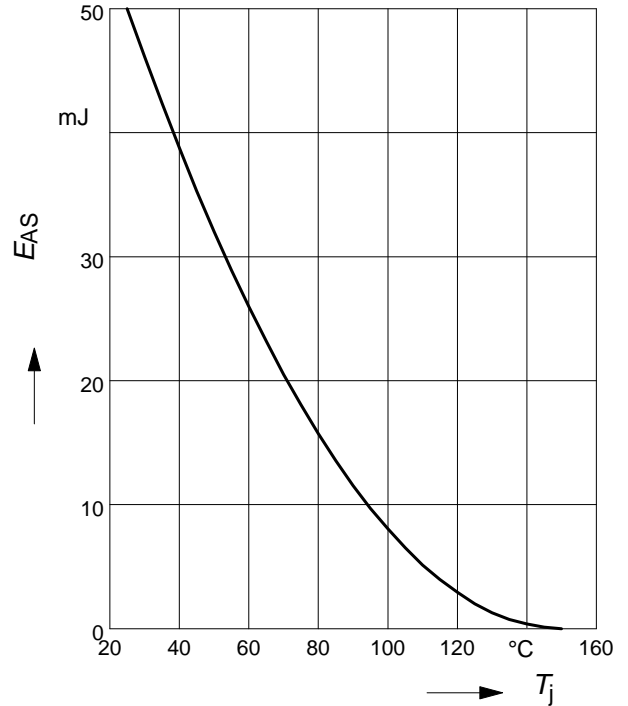
par.: $T_j \leq 150\text{ }^\circ\text{C}$



14 Avalanche energy

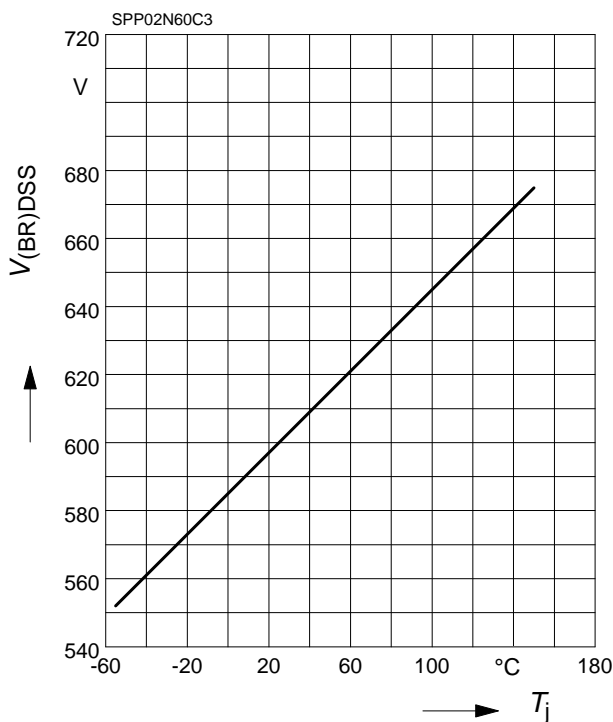
$$E_{AS} = f(T_j)$$

par.: $I_D = 0.9\text{ A}$, $V_{DD} = 50\text{ V}$



15 Drain-source breakdown voltage

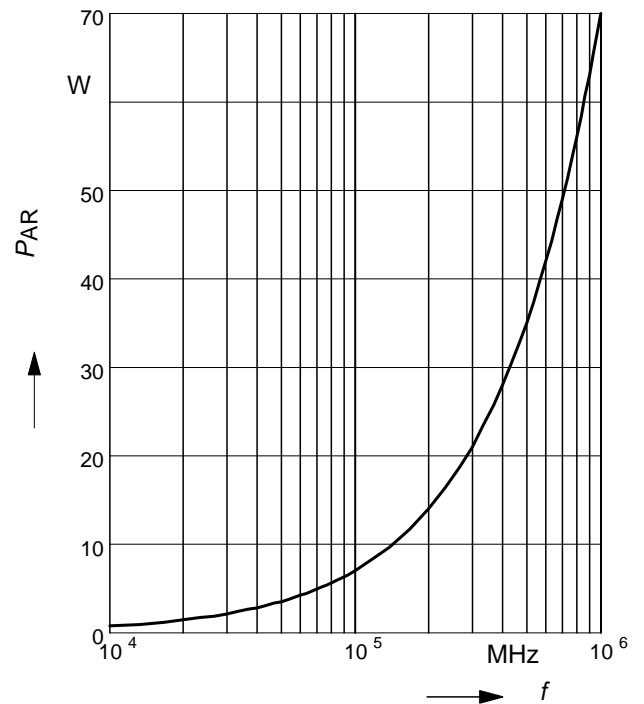
$$V_{(BR)DSS} = f(T_j)$$



16 Avalanche power losses

$$P_{AR} = f(f)$$

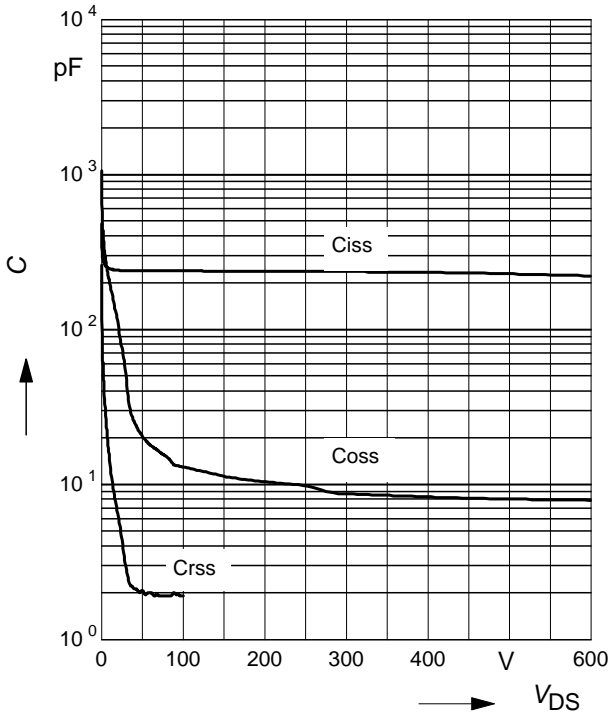
parameter: $E_{AR} = 0.07\text{ mJ}$



17 Typ. capacitances

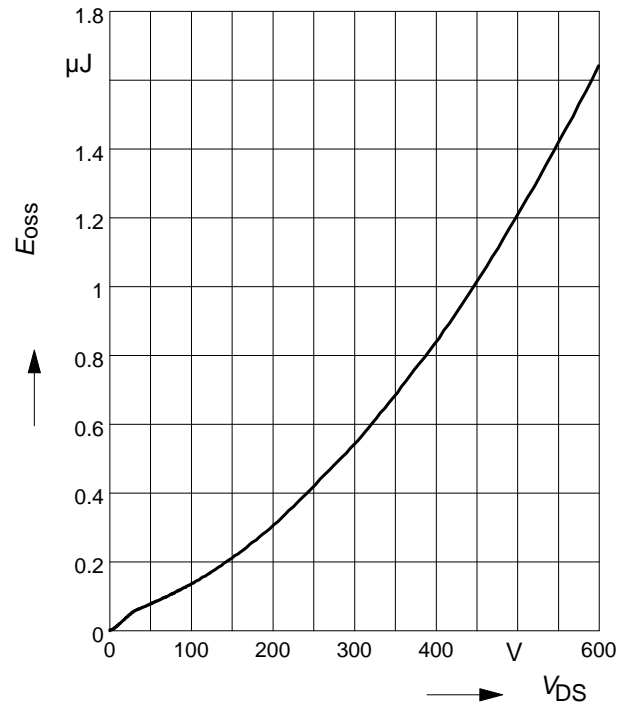
$$C = f(V_{DS})$$

parameter: $V_{GS}=0V, f=1\text{ MHz}$

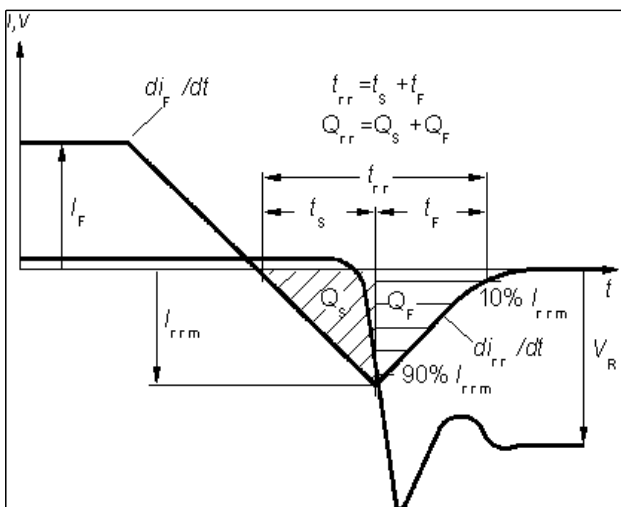


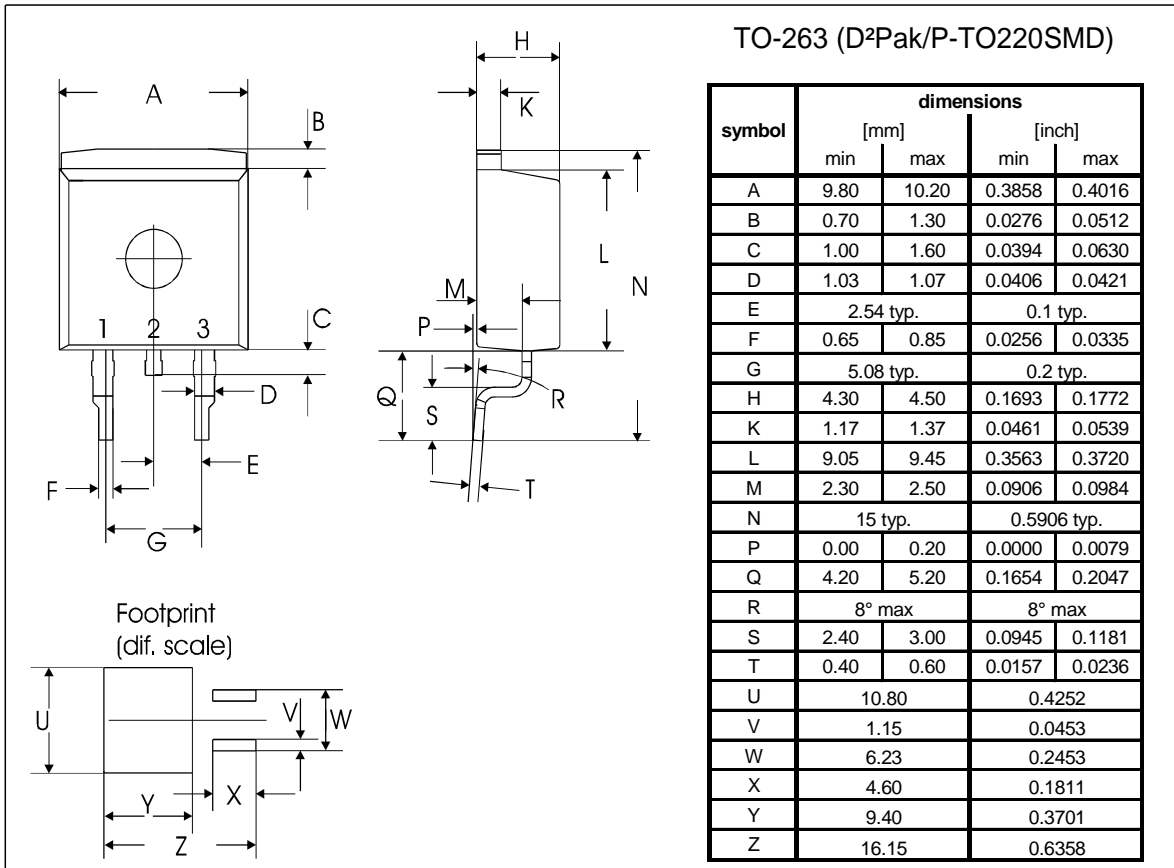
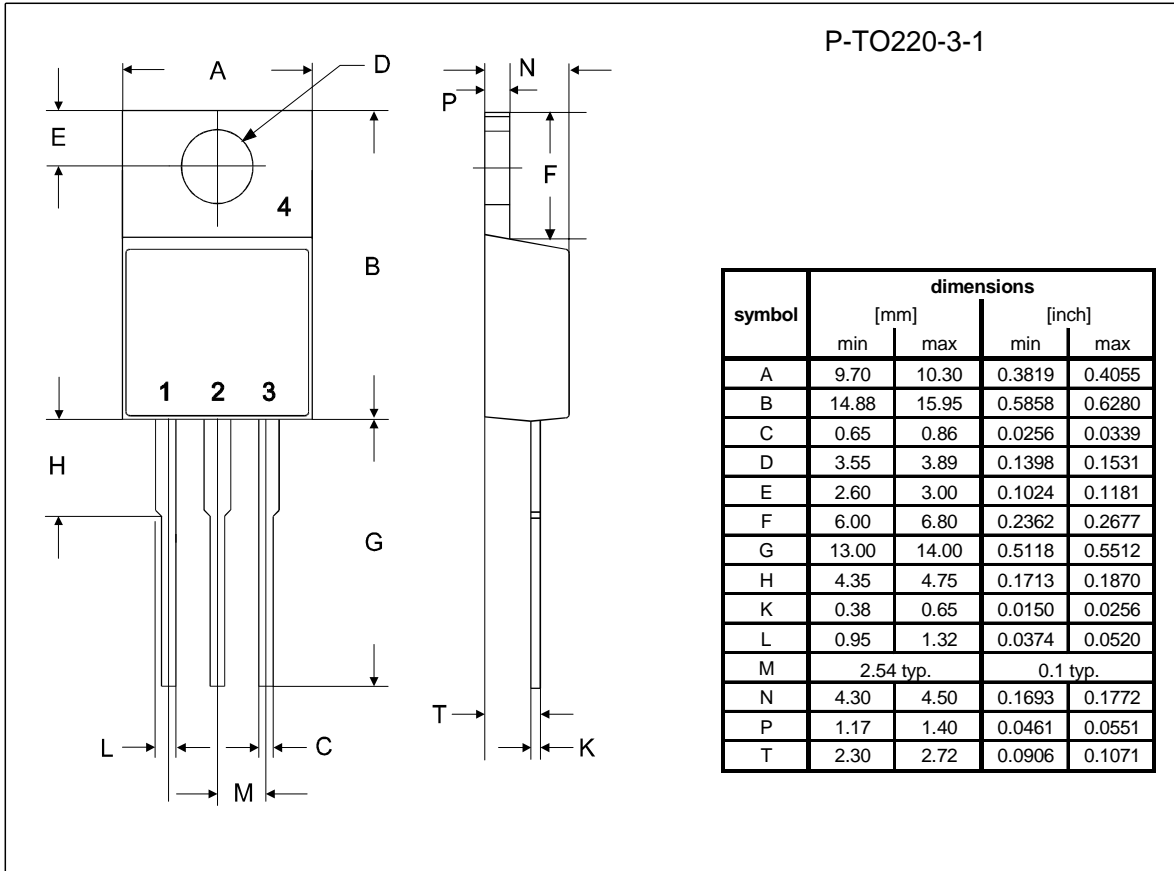
18 Typ. C_{OSS} stored energy

$$E_{OSS} = f(V_{DS})$$



Definition of diodes switching characteristics





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